



PHP18NQ10T,127 Information



For Reference Only

Part Number PHP18NQ10T,127 **Manufacturer** Nexperia USA Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 18A TO220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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PHP18NQ10T,127 Specifications

Manufacturer Part Number PHP18NQ10T,127 Manufacturer Nexperia USA Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 21nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 633pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 90 mOhm @ 9A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220A		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 1nput Capacitance (Ciss) (Max) @ Vds 420V FET Feature -Power Dissipation (Max) Test Feature Power Dissipation (Max) Poerating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB To-220AB	Manufacturer Part Number	PHP18NQ10T,127
Package TO-220-3 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ ImA Gate Charge (Qg) (Max) @ Vgs 21nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 633pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 90 mOhm @ 9A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Manufacturer	Nexperia USA Inc.
Package TO-220-3 Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 21nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 633pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 90 mOhm @ 9A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Category	Discrete Semiconductor Products
Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 21nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 633pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 90 mOhm @ 9A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C18A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 1mAGate Charge (Qg) (Max) @ Vgs21nC @ 10VInput Capacitance (Ciss) (Max) @ Vds633pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)79W (Tc)Rds On (Max) @ Id, Vgs90 mOhm @ 9A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 18A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **EUV** FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case MOSFET (Metal Oxide) 100V 100V 18A (Tc) 10V 4V @ 1mA 4V @ 1mA 4V @ 1mA 633pF @ 25V 221nC @ 10V 633pF @ 25V **EUV** FET Feature - CPOWD (Tc) 90 mOhm @ 9A, 10V Operating Temperature -55°C ~ 175°C (TJ) Through Hole To-220AB Package / Case	Series	TrenchMOS?
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C18A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 1mAGate Charge (Qg) (Max) @ Vgs21nC @ 10VInput Capacitance (Ciss) (Max) @ Vds633pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)79W (Tc)Rds On (Max) @ Id, Vgs90 mOhm @ 9A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature For Vgs (Max) FET Peature Power Dissipation (Max) Toput (Ciss) (Max) @ Id, Vgs Toput (Cits) (Max) (Max) (Cits) (Max) (Cits) (Max) (Cits) (Max) (Cits) (Max) (Cits) (Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **ET Feature** Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB TO-220-3	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 633pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 90 mOhm @ 9A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Current - Continuous Drain (Id) @ 25°C	18A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 633pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 90 mOhm @ 9A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 633pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 90 mOhm @ 9A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)79W (Tc)Rds On (Max) @ Id, Vgs90 mOhm @ 9A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	21nC @ 10V
FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 90 mOhm @ 9A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	633pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 90 mOhm @ 9A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs90 mOhm @ 9A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	79W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	90 mOhm @ 9A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

PHP18NQ10T,127 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

PHP18NQ10T,127 Payment Methods



















PHP18NQ10T,127 Shipping Methods













If you have any question about PHP18NQ10T,127, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com